

Power MOSFET



P-Channel MOSFET

FEATURES

- Dynamic dV/dt rating
- Repetitive avalanche rated
- For automatic insertion
- End stackable
- P-channel
- Fast switching
- Ease of paralleling
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT

PRODUCT SUMMARY

| | | |
|---------------------------|------------------|-----|
| V_{DS} (V) | -200 | |
| $R_{DS(on)}$ (Ω) | $V_{GS} = -10$ V | 3.0 |
| Q_g (Max.) (nC) | 8.9 | |
| Q_{gs} (nC) | 2.1 | |
| Q_{gd} (nC) | 3.9 | |
| Configuration | Single | |

DESCRIPTION

The power MOSFETs technology is the key to Vishay advanced line of power MOSFET transistors. The efficient geometry and unique processing of the power MOSFETs design achieve very low on-state resistance combined with high transconductance and extreme device ruggedness.

The 4 pin DIP package is a low cost machine-insertable case style which can be stacked in multiple combinations on standard 0.1" pin centers. The dual drain serves as a thermal link to the mounting surface for power dissipation levels up to 1 W.

ORDERING INFORMATION

| | |
|----------------|-------------|
| Package | HVMDIP |
| Lead (Pb)-free | IRFD9210PbF |

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

| PARAMETER | SYMBOL | LIMIT | UNIT |
|--|----------------|------------------|-------|
| Drain-source voltage | V_{DS} | -200 | V |
| Gate-source voltage | V_{GS} | ± 20 | |
| Continuous drain current | I_D | $T_A = 25$ °C | -0.40 |
| | | $T_A = 100$ °C | -0.25 |
| Pulsed drain current ^a | I_{DM} | -3.2 | A |
| Linear derating factor | | 0.0083 | W/°C |
| Single pulse avalanche energy ^b | E_{AS} | 210 | mJ |
| Repetitive avalanche current ^a | I_{AR} | -0.40 | A |
| Repetitive avalanche energy ^a | E_{AR} | 0.10 | mJ |
| Maximum power dissipation | P_D | 1.0 | W |
| Peak diode recovery dv/dt ^c | dV/dt | -5.0 | V/ns |
| Operating junction and storage temperature range | T_J, T_{stg} | -55 to + 150 | °C |
| Soldering rRecommendations (peak temperature) ^d | For 10 s | 300 ^d | |

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- $V_{DD} = -50$ V, starting $T_J = 25$ °C, $L = 123$ mH, $R_g = 25$ Ω , $I_{AS} = -1.6$ A (see fig. 12)
- $I_{SD} \leq -2.3$ A, $dI/dt \leq 70$ A/ μ s, $V_{DD} \leq V_{DS}$, $T_J \leq 150$ °C
- 1.6 mm from case



| THERMAL RESISTANCE RATINGS | | | | |
|-----------------------------|------------|------|------|------|
| PARAMETER | SYMBOL | TYP. | MAX. | UNIT |
| Maximum Junction-to-Ambient | R_{thJA} | - | 120 | °C/W |

| SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted) | | | | | | | |
|---|---------------------|---|---|------|-------|-----------|---------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNIT |
| Static | | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$ | | -200 | - | - | V |
| V_{DS} Temperature Coefficient | $\Delta V_{DS}/T_J$ | Reference to $25\text{ }^\circ\text{C}$, $I_D = -1\text{ mA}$ | | - | -0.23 | - | V/°C |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$ | | -2.0 | - | -4.0 | V |
| Gate-Source Leakage | I_{GSS} | $V_{GS} = \pm 20\text{ V}$ | | - | - | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = -200\text{ V}, V_{GS} = 0\text{ V}$ | | - | - | -100 | μA |
| | | $V_{DS} = -160\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$ | | - | - | -500 | |
| Drain-Source On-State Resistance | $R_{DS(on)}$ | $V_{GS} = -10\text{ V}$ | $I_D = -0.24\text{ A}^b$ | - | - | 3.0 | Ω |
| Forward Transconductance | g_{fs} | $V_{DS} = -50\text{ V}, I_D = -0.24\text{ A}$ | | 0.27 | - | - | S |
| Dynamic | | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0\text{ V}, V_{DS} = -25\text{ V}, f = 1.0\text{ MHz}$, see fig. 5 | | - | 170 | - | pF |
| Output Capacitance | C_{oss} | | | - | 54 | - | |
| Reverse Transfer Capacitance | C_{rss} | | | - | 16 | - | |
| Total Gate Charge | Q_g | $V_{GS} = -10\text{ V}$ | $I_D = -1.3\text{ A}, V_{DS} = -160\text{ V}$ see fig. 6 and 13 ^b | - | - | 8.9 | nC |
| Gate-Source Charge | Q_{gs} | | | - | - | 2.1 | |
| Gate-Drain Charge | Q_{gd} | | | - | - | 3.9 | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = -100\text{ V}, I_D = -2.3\text{ A}$ $R_g = 24\text{ }\Omega, R_D = 41\text{ }\Omega$, see fig. 10 ^b | | - | 8.0 | - | ns |
| Rise Time | t_r | | | - | 12 | - | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | - | 11 | - | |
| Fall Time | t_f | | | - | 13 | - | |
| Internal Drain Inductance | L_D | Between lead, 6 mm (0.25") from package and center of die contact | | - | 4.0 | - | nH |
| Internal Source Inductance | L_S | | | - | 6.0 | - | |
| Drain-Source Body Diode Characteristics | | | | | | | |
| Continuous Source-Drain Diode Current | I_S | MOSFET symbol showing the integral reverse p - n junction diode | | - | - | -0.40 | A |
| Pulsed Diode Forward Current ^a | I_{SM} | | | - | - | -3.2 | |
| Body Diode Voltage | V_{SD} | $T_J = 25\text{ }^\circ\text{C}, I_S = -0.40\text{ A}, V_{GS} = 0\text{ V}^b$ | | - | - | -5.8 | V |
| Body Diode Reverse Recovery Time | t_{rr} | $T_J = 25\text{ }^\circ\text{C}, I_F = -2.3\text{ A}, di/dt = 100\text{ A}/\mu\text{s}^b$ | | - | 110 | 220 | ns |
| Body Diode Reverse Recovery Charge | Q_{rr} | | | - | 0.56 | 1.1 | μC |

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\text{ }\%$

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

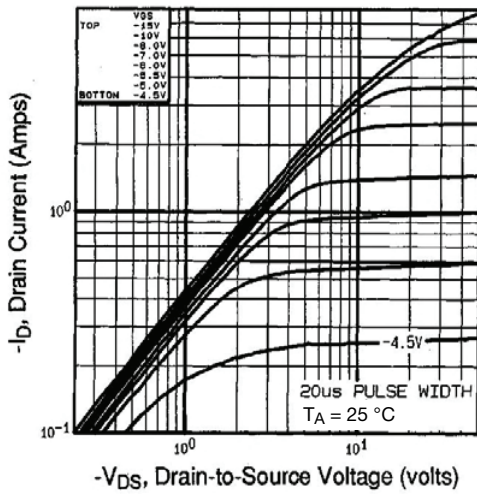


Fig. 1 - Typical Output Characteristics, $T_A = 25\text{ }^\circ\text{C}$

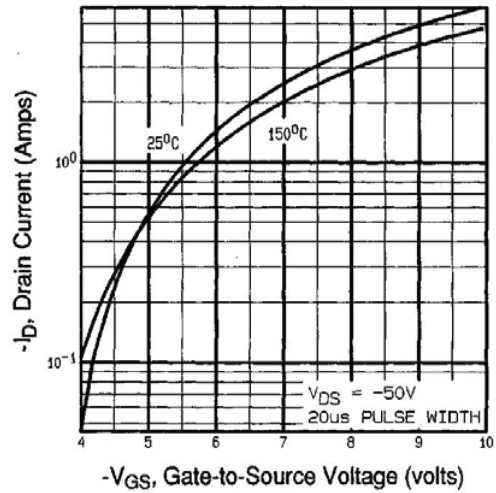


Fig. 3 - Typical Transfer Characteristics

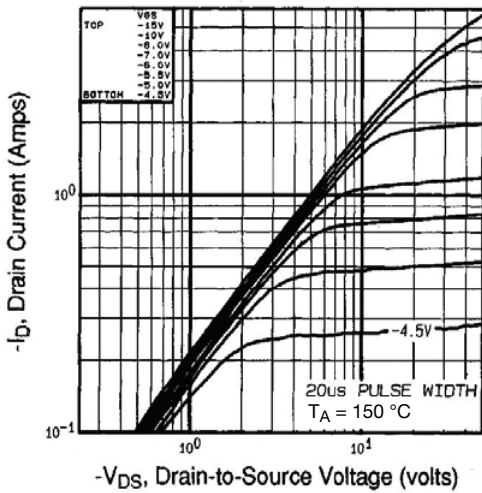


Fig. 2 - Typical Output Characteristics, $T_A = 150\text{ }^\circ\text{C}$

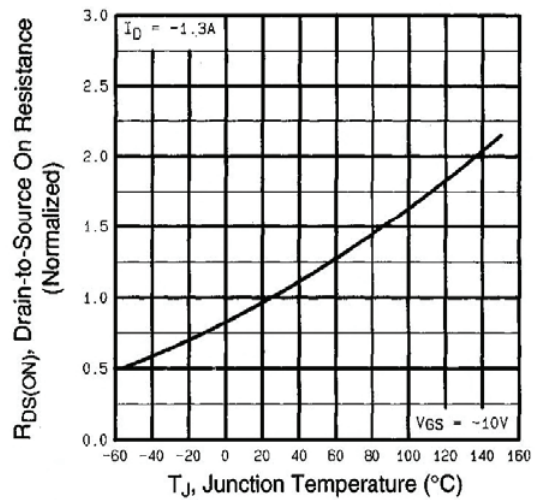


Fig. 4 - Normalized On-Resistance vs. Temperature

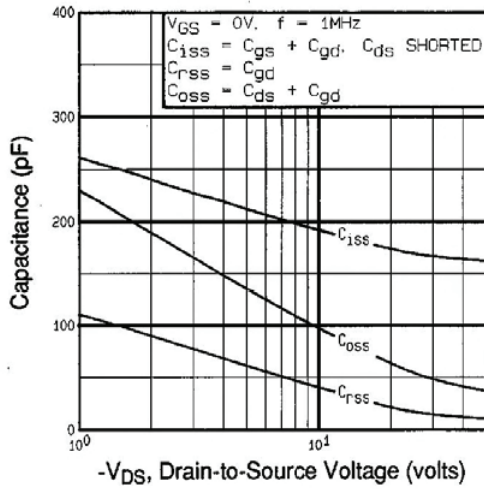


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

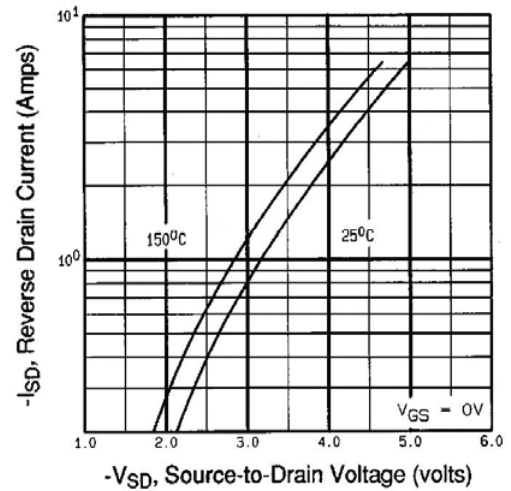


Fig. 7 - Typical Source-Drain Diode Forward Voltage

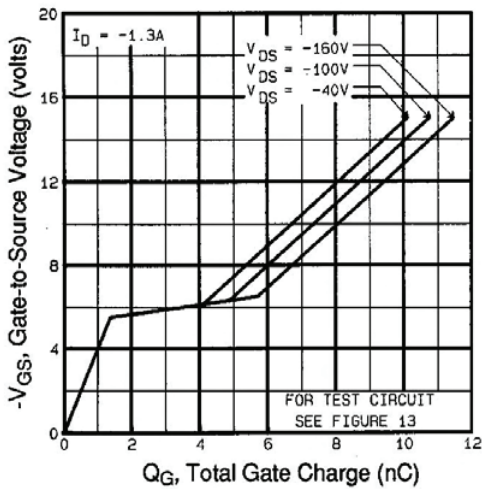


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

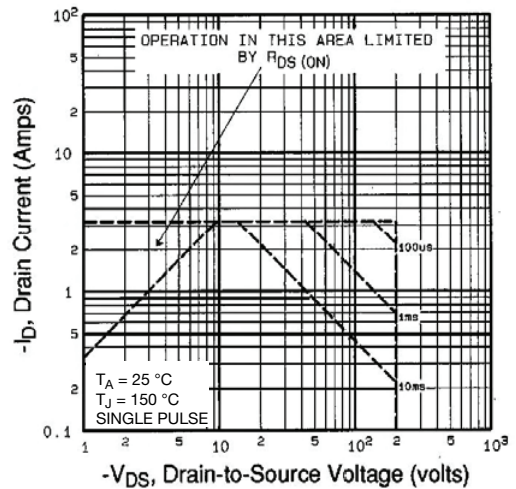


Fig. 8 - Maximum Safe Operating Area

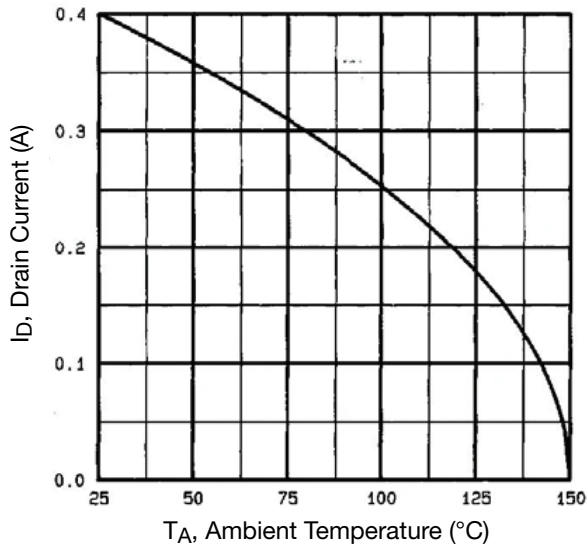


Fig. 9 - Maximum Drain Current vs. Ambient Temperature

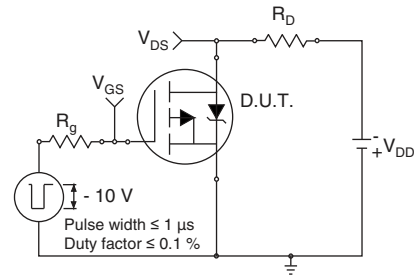


Fig. 10a - Switching Time Test Circuit

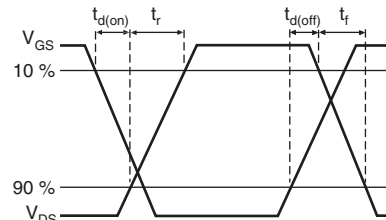


Fig. 10b - Switching Time Waveforms

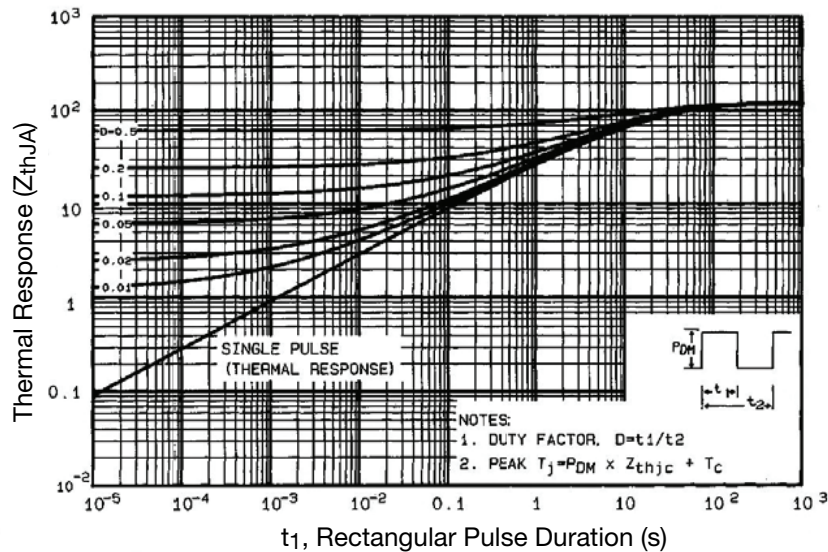


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

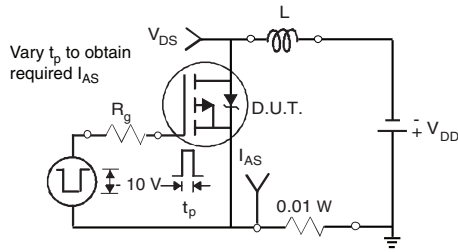


Fig. 12a - Unclamped Inductive Test Circuit

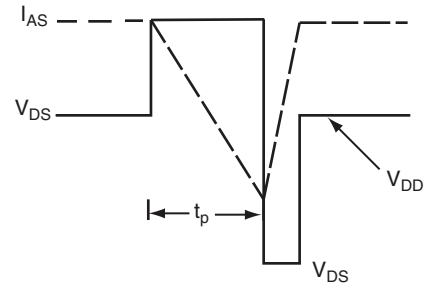


Fig. 12b - Unclamped Inductive Waveforms

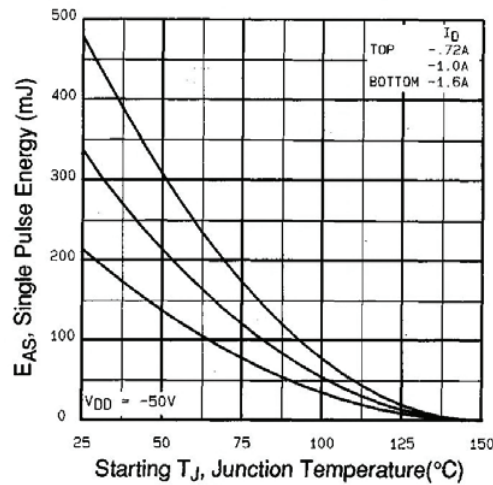


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

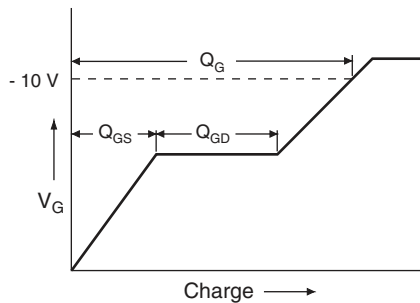


Fig. 13a - Basic Gate Charge Waveform

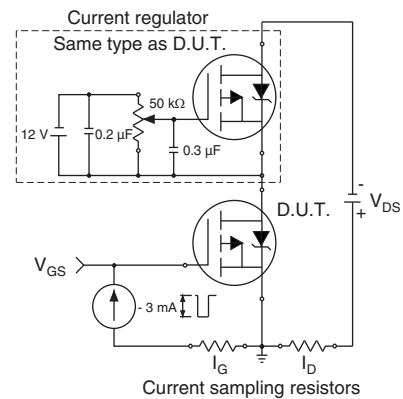
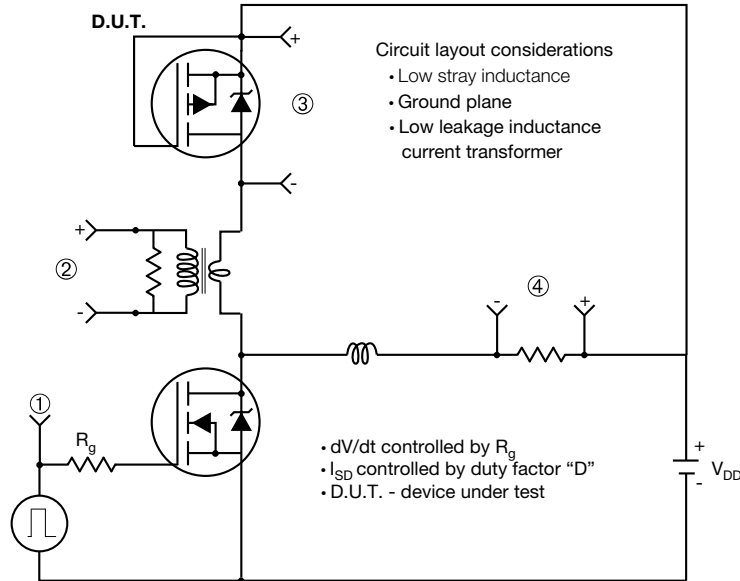


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



Note
• Compliment N-Channel of D.U.T. for driver



Fig. 14 - For P-Channel

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HVM DIP (High voltage)



| DIM. | INCHES | | MILLIMETERS | |
|------|--------|-------|-------------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| A | 0.310 | 0.330 | 7.87 | 8.38 |
| E | 0.300 | 0.425 | 7.62 | 10.79 |
| L | 0.270 | 0.290 | 6.86 | 7.36 |

ECN: X10-0386-Rev. B, 06-Sep-10
DWG: 5974

Note

- Package length does not include mold flash, protrusions or gate burrs. Package width does not include interlead flash or protrusions.



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